

C2 Sub 22

4. (Three Times Amended) A semiconductor device comprising:  
an insulated gate field effect transistor comprising a pair of main electrodes used as source and drain electrodes, an insulating gate film adjacent to the pair of main electrodes, and a gate electrode comprising a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the first region, the first region and the second region having an identical conductivity type; and  
a silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second group IV element.

C3 Sub 23

11. (Three Times Amended) A semiconductor device comprising:  
an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, an insulating gate film adjacent to the pair of main electrodes, and a gate electrode comprising a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including a multiple element compound including at least the first and second group IV elements and metal, and formed on the first region, the first region and the second region having an identical conductivity type; and  
a silicide electrode formed in contact with the second region of the gate electrode, including the first group IV element and metal, and being substantially free from the second group IV element.

C4 Sub 23

23. (Three Times Amended) A semiconductor device comprising:  
an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, an insulating gate film adjacent to the pair of main electrodes, and a gate electrode comprising a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the first region, the first region and the second region having an identical conductivity type;

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a respective elevated electrode formed on the main electrodes, and having a third region including a third group IV element and a fourth group IV element and a fourth region formed on the third region and including the third group IV element;

a first silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second group IV element; and

a second silicide electrode formed in contact with the fourth region of the elevated electrode, and being substantially free from the fourth group IV element.

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